



45A, 60V N-CHANNEL POWER MOSFET

PDFN5060-8L(Prefix :L)

Description

This model is an n-channel enhanced MOS power field effect transistor manufactured by silicon epitaxial process.

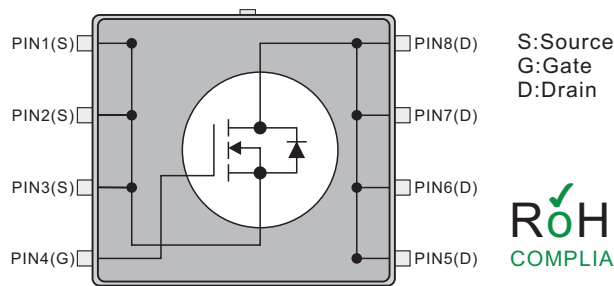
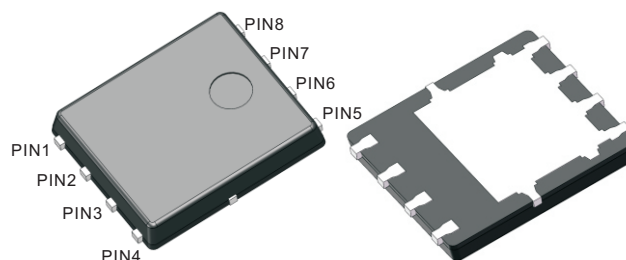
This model has excellent switching characteristics, extremely low on impedance, low gate charge and other characteristics.

Features

- $R_{DS(ON)} < 12 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=20\text{A}$
- Extremely low on impedance
- Low gate charge
- Superior switching characteristics
- 100% Avalanche tested
- 100% ΔV_{DS} tested

Mechanical data

- Case: PDFN5060-8L
- Approx. Weight:0.093g (0.0032oz)
- Lead free finish, RoHS compliant
- Case Material: "Green" molding compound, UL flammability classification 94V-0, "Halogen-free".



Packing Marking And Ordering Information

Device Package	Device	Marking	Packing Type	QTY Per Reel	Inner box	Per Carton
PDFN5060-8L	L8R8NS60R	L8R8NS60R	Reel	5,000 Pcs	10,000 Pcs	50,000 Pcs

Absolute Maximum Ratings (Ta=25°C, Unless Otherwise Specified)

Parameter	Symbols	Ratings	Units
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	I_D	45 32	A
Pulsed Drain Current (Note 2)	I_{DM}	180	A
Avalanche Energy Single Pulsed (Note 3)	E_{AS}	100	mJ
Power Dissipation (TA = 25°C, Steady State)	P_D	83	W
Operating junction and storage temperature	T_J, T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L=0.5mH, IAS=20A, VDD = 90V, RG = 25 Ω , Starting TJ = 25°C

Thermal Resistance

Parameter	Symbols	Ratings	Units
Thermal resistance, junction – case.	R_{thJC}	1.5	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	63	°C/W



Electrical Characteristics (Ta=25°C, Unless Otherwise Specified)

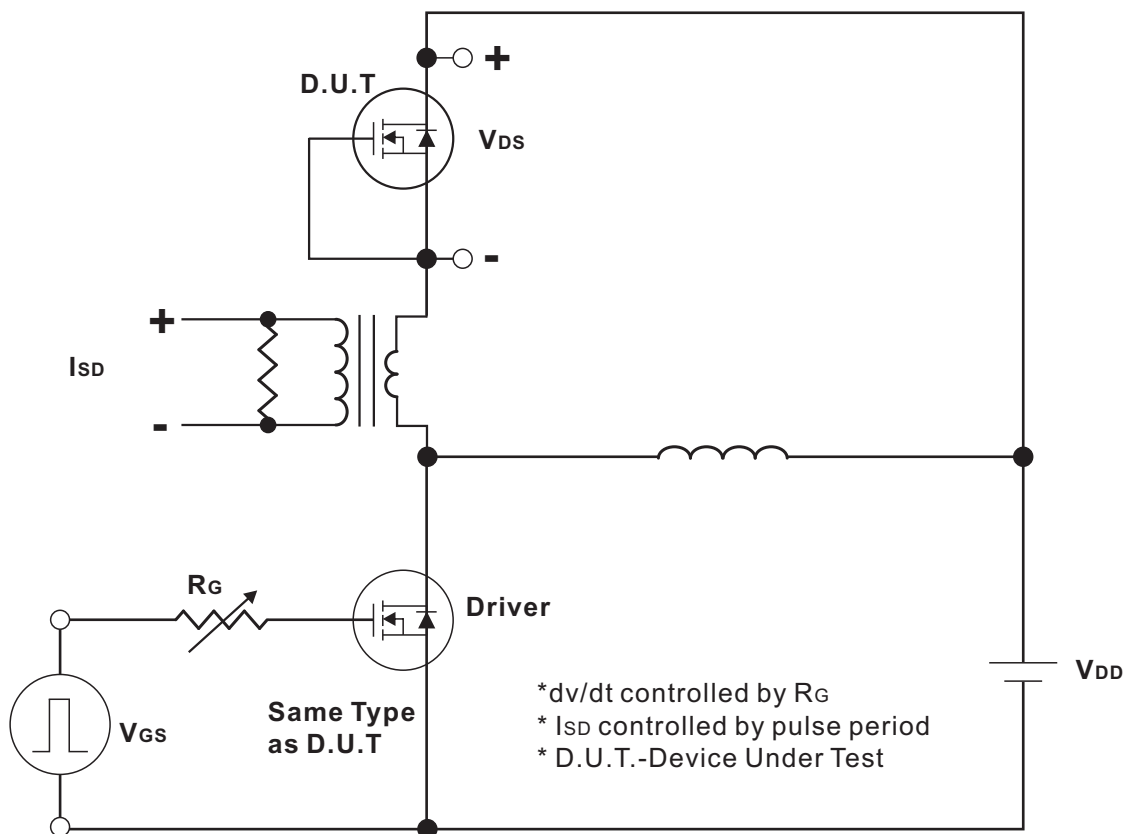
Parameter	Symbols	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		8.8	12	m Ω
Transconductance	g_{fs}	$V_{DS}=10V, I_D=20A$		14		S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	$V_{DS}=40V,$		935		pF
Output Capacitance	C_{OSS}	$V_{GS}=0V,$		214		pF
Reverse Transfer Capacitance	C_{RSS}	$f=1.0MHz$		15		pF
Gate resistance	R_G			1.8		Ω
Switching Characteristics						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=40V, V_{GS}=10V,$		36		nC
Gate-Source Charge	Q_{GS}	$I_D=20A(NOTE1,2)$		10		nC
Gate-Drain Charge	Q_{GD}			5		nC
Turn-On Delay Time (Note 1)	$t_{D(ON)}$	$V_{DS}=40V, V_{GS}=10V,$		10		ns
Turn-On Rise Time	t_R	$R_G=3\Omega, I_D=20A$		7		ns
Turn-Off Delay Time	$t_{D(OFF)}$	(NOTE1,2)		30		ns
Turn-Off Fall Time	t_F			15		ns
Drain-source Diode Characteristics And Maximum Ratings						
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_{SD}=20A, V_{GS}=0V$			1.2	V
Diode continuous forward current	I_S				45	A

Notes:

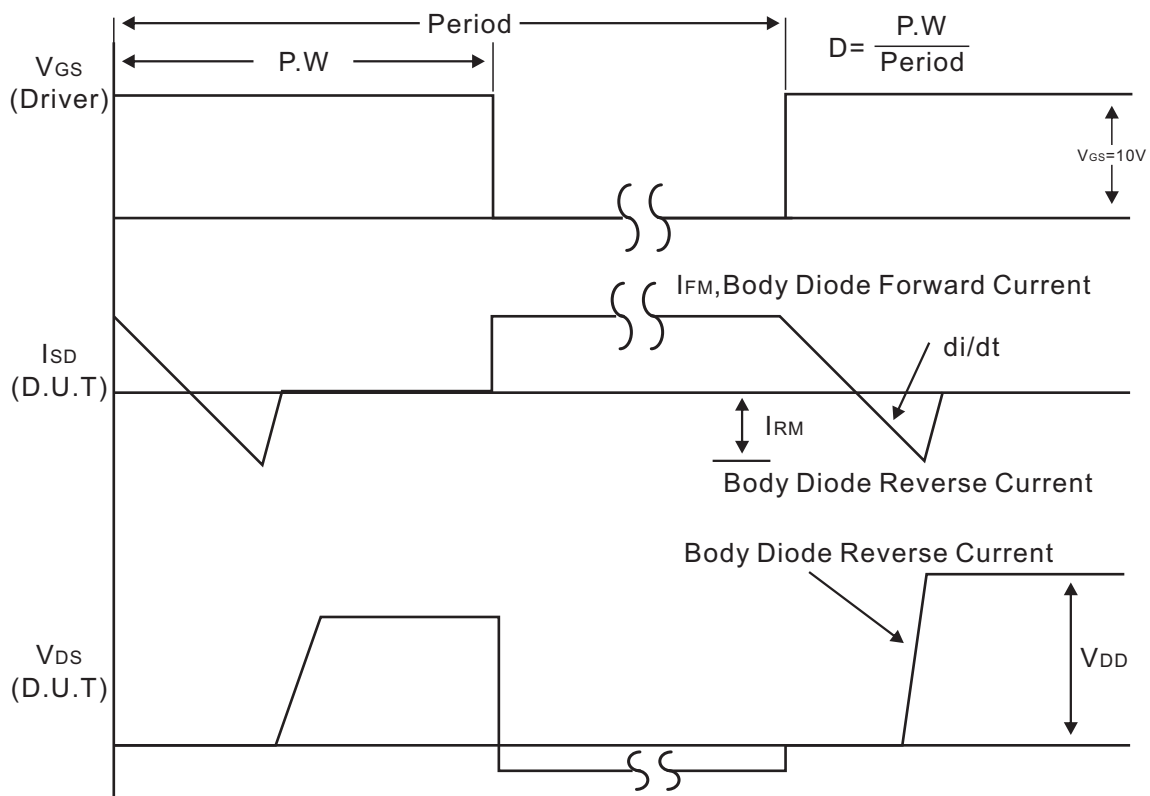
1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature.



Test Circuits and waveforms



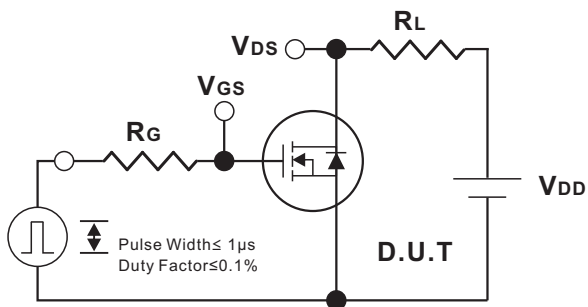
Peak Diode Recovery dv/dt Test Circuit



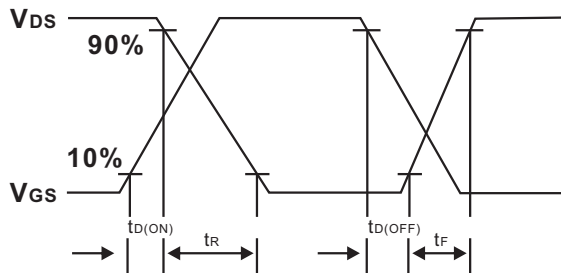
Peak Diode Recovery dv/dt Waveforms



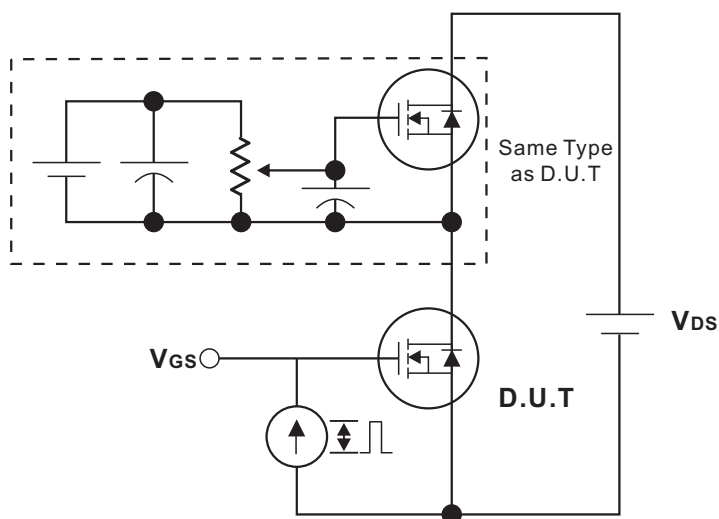
Test Circuits and waveforms



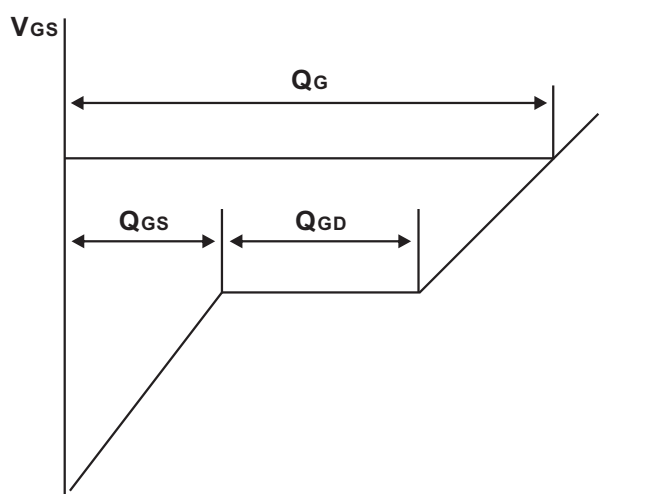
Switching Test Circuit



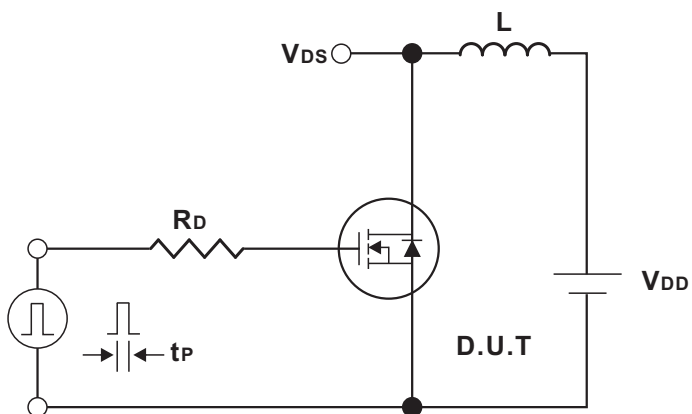
Switching Waveforms



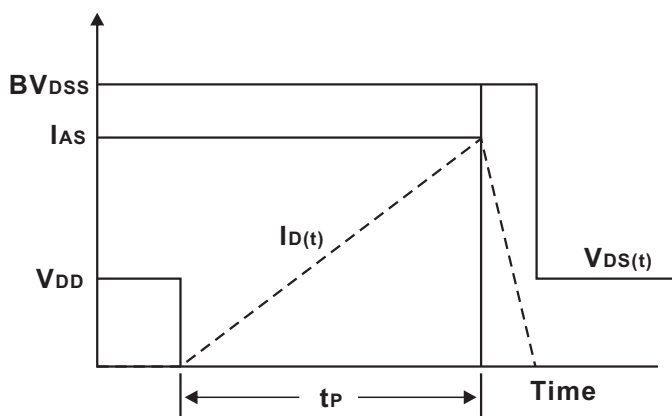
Gate Charge Test Circuit



Charge Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



Typical Characteristics

Fig.1 Output characteristics

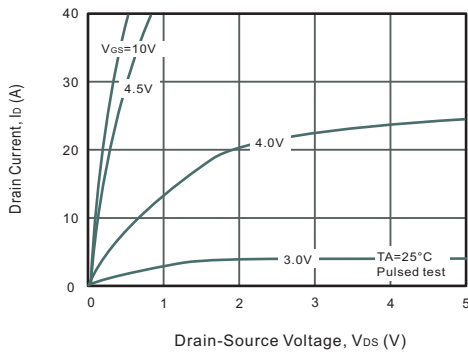


Fig.2 Power Dissipation

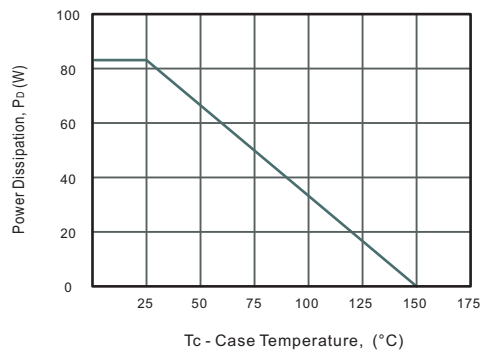


Fig.3 Drain Current Derating

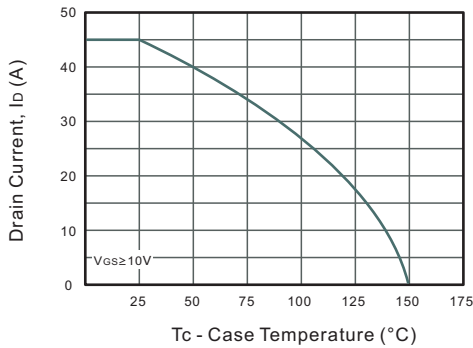


Fig.4 Drain-Source On-Resistance vs. Drain Current

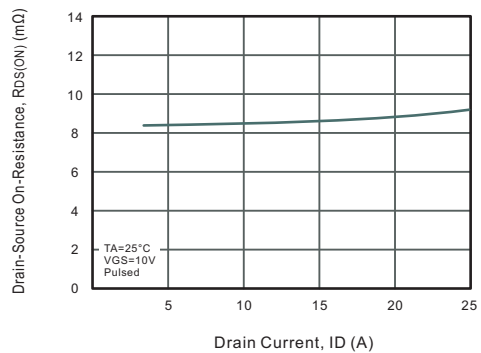


Fig.5 Gate Threshold Voltage vs. Junction Temperature

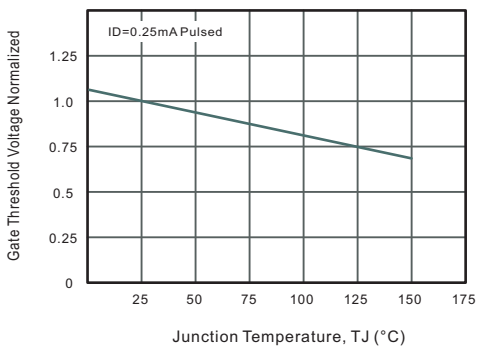


Fig.6 Body-diode Forward Characteristics

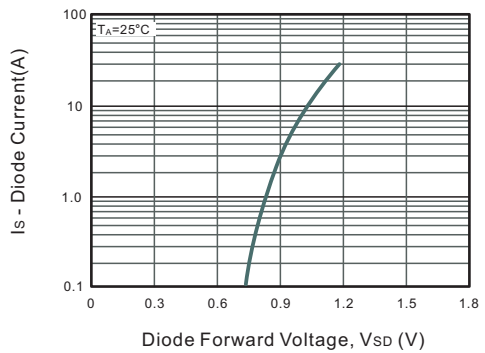


Fig.7 Drain-Source On-Resistance vs. Junction Temperature

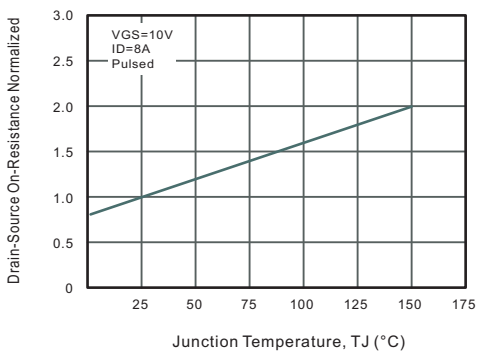
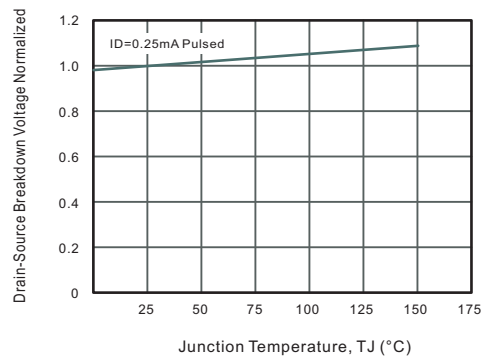
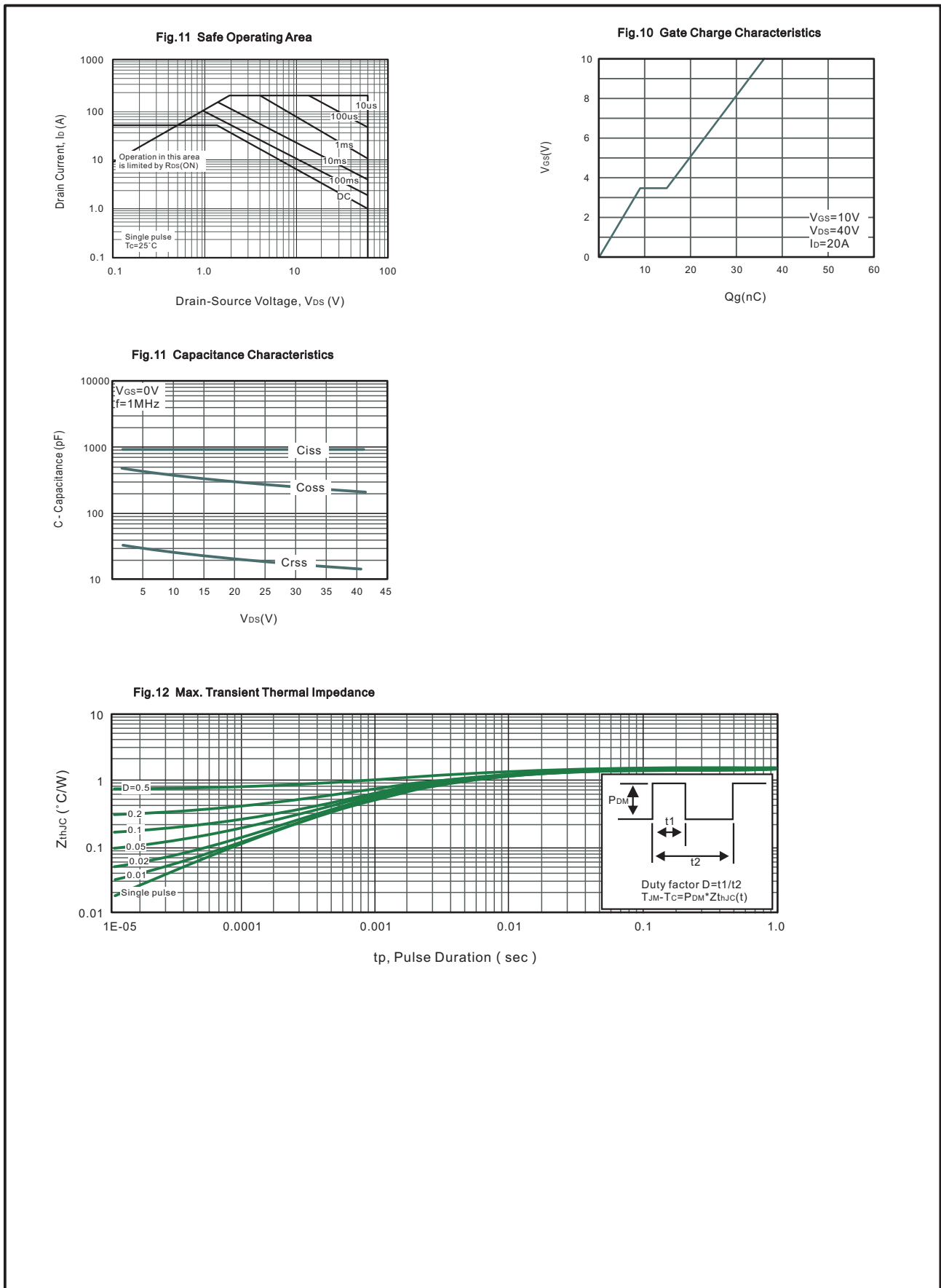


Fig.8 Breakdown Voltage vs. Junction Temperature





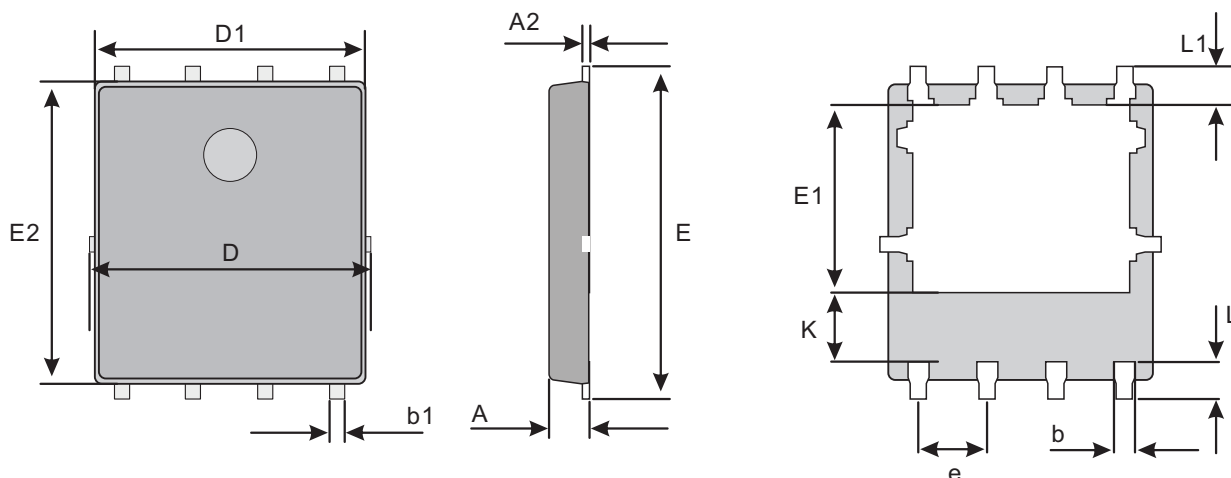
Typical Characteristics





Package Outline
Plastic surface mounted package;8 leads

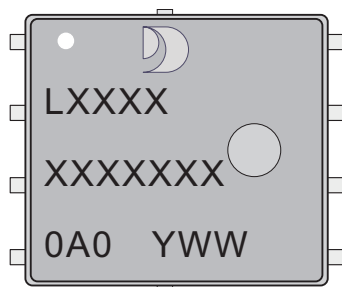
PDFN5060-8L



Mechanical data

UNIT		A	A2	b	b1	D	D1	E	E1	E2	e	K	L	L1
mm	max	1.1	0.304	0.4 ref.	0.4	5.3	5.24	6.35	3.675	6.09	1.27 typ.	1.29 typ.	0.785	0.7 typ.
	typ	1.0	0.254		0.3	5.15	5.04	6.15	3.475	5.89			0.685	
	min	0.9	0.204		0.2	5.0	4.84	5.95	3.275	5.69			0.585	
mil	max	43	12	16 ref.	16	209	206	250	145	240	50 typ.	51 typ.	31	28 typ.
	typ	39	10		12	203	198	242	137	232			27	
	min	35	8		8	197	191	234	129	224			23	

Marking Diagram



- Jingdao Logo
 - Unmarkable Surfacea
 - Pin1 Mark
- LXXXX XXXXXXXX: Marking code
0A0: Traceability code
YWW: Y: Years(0~9)
WW: Week



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